

3-phase bridge rectifier + brake chopper + 3-phase

bridge inverter SK 100 DGDL 066 T

Target Data

Features

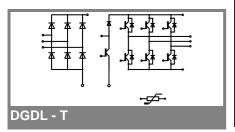
- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology free-wheeling diode
- Integrated NTC temperatur sensor

Typical Applications

- Inverter up to 12,5 kVA
- Typical motor power 5,5 kW

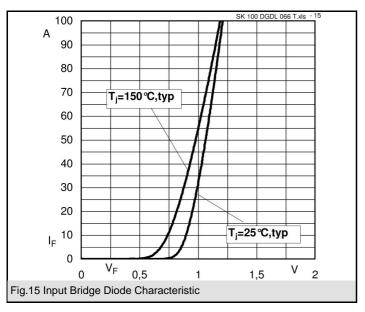
Remarks

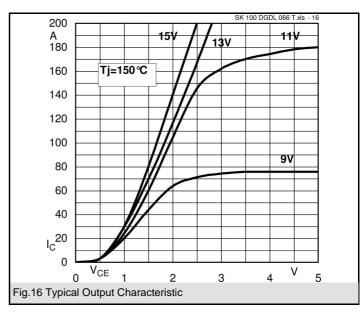
• V_{CE.sat} , V_F = chip level value

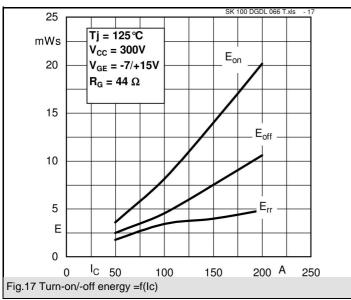


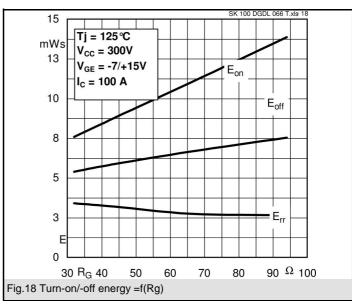
Absolute Maximum Ratings T _s = 25°C, unless otherwise specified							
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V _{CES} I _C	T _s = 25 (70) °C, T _i = 175 °C	600 106 (85)	V A				
I _C	$T_s = 25 (70) ^{\circ}\text{C}, T_j = 150 ^{\circ}\text{C}$	96 (73)	Α				
I _{CRM}	$I_{CRM} = 2 \times I_{Cnom}, t_p = 1 \text{ ms}$	200	Α				
V_{GES}		± 20	V				
T _j		-40 + 175	°C				
Diode - Inverter, Chopper							
I _F	$T_s = 25 (70) ^{\circ}C, T_i = 150 ^{\circ}C$	91 (67)	Α				
I _F	$T_s = 25 (70) ^{\circ}C, T_j = 175 ^{\circ}C$	99 (79)	Α				
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$		128				
Diode - Rectifier							
V_{RRM}		800	V				
I _F	$T_s = 70 ^{\circ}C$	61	Α				
I _{FSM}	$t_p = 10 \text{ ms, sin } 180 ^\circ, T_j = 25 ^\circ\text{C}$	700	Α				
i²t	$t_p = 10 \text{ ms, sin } 180 ^\circ, T_j = 25 ^\circ\text{C}$	2400	A²s				
T _j		-40 + 175	°C				
T _{sol}	Terminals, 10 s	260	°C				
T _{stg}		-40 + 125	°C				
V _{isol}	AC, 1 min.	2500	V				

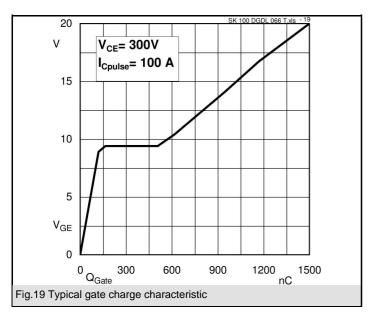
Characteristics T _s = 25°C, unless otherwise spe					ecified			
Symbol	Conditions	min.	typ.	max.	Units			
IGBT - Inverter, Chopper								
V _{CE(sat)}	I _{Cnom} = 100 A, T _i = 25 (150) °C	1,05	1,45 (1,7)	1,9 (2,15)	V			
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 1.6$ mA	5	5,8	6,5	V			
$V_{CE(TO)}$	T _j = 25 (150) °C		0,9 (0,7)	1 (0,8)	V			
r_{CE}	$T_j = 25 (150) ^{\circ}C$		5,5 (10)	9 (13,5)	mΩ			
C _{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		6,16		nF			
C _{oes}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,38		nF			
C _{res}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,18		nF			
$R_{th(j-s)}$	per IGBT		0,65		K/W			
t _{d(on)}	under following conditions		134		ns			
t _r	$V_{CC} = 300 \text{ V}, V_{GE} = -7 / + 15 \text{ V}$		125		ns			
t _{d(off)}	I_{Cnom} = 100 A, T_j = 125 °C		1131		ns			
t _f	$R_{Gon} = R_{Goff} = 44 \Omega$		86		ns			
$E_{on} \left(E_{off} \right)$	inductive load		8,1 (4,5)		mJ			
Diode - Inverter, Chopper								
$V_F = V_{EC}$	I _F = 100 A, T _i = 25 (150) °C		1,25 (1,2)		V			
V _(TO)	T _i = 25 (150) °C		0,95 (0,85)		V			
r _T	T _j = 25 (150) °C		3 (3,5)		mΩ			
$R_{th(j-s)}$	per diode		0,8		K/W			
I _{RRM}	under following conditions		40		Α			
Q_{rr}	$I_{Fnom} = 100 \text{ A}, V_{R} = 300 \text{ V}$		20		μC			
E _{rr}	$V_{GE} = 0 \text{ V}, T_j = 125^{\circ}\text{C}$		3,4		mJ			
	$di_F/dt = 2575 A/\mu s$							
Diode - Rectifier								
V_{F}	I _{Fnom} = 35 A, T _j = 25 °C		1,1		V			
$V_{(TO)}$	T _i = 150 °C		0,8		V			
r _T	$T_{j} = 150 ^{\circ}\text{C}$		11		mΩ			
$R_{th(j-s)}$	per diode		0,9		K/W			
Temperature Sensor								
R _{ts}	5 %, T _r = 25 (100) °C		5000(493)		Ω			
Mechanical Data								
w			60		g			
M_s	Mounting torque		3,5		Nm			

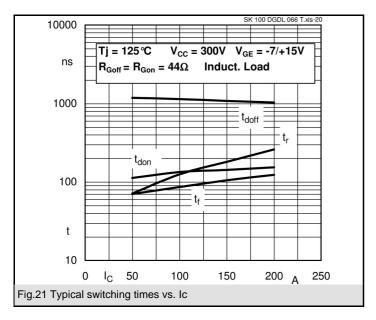


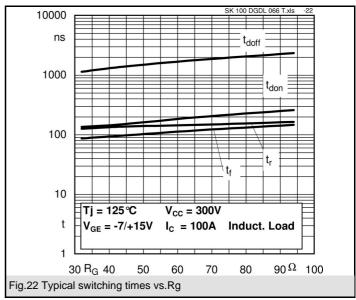


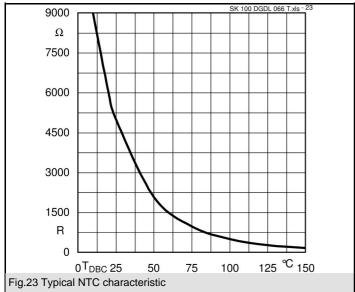


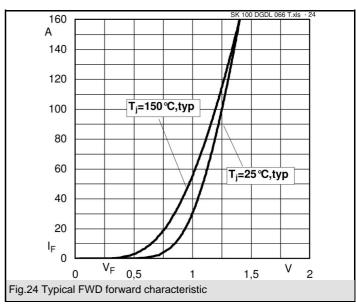


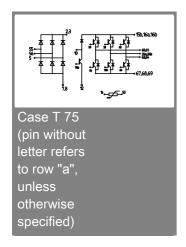


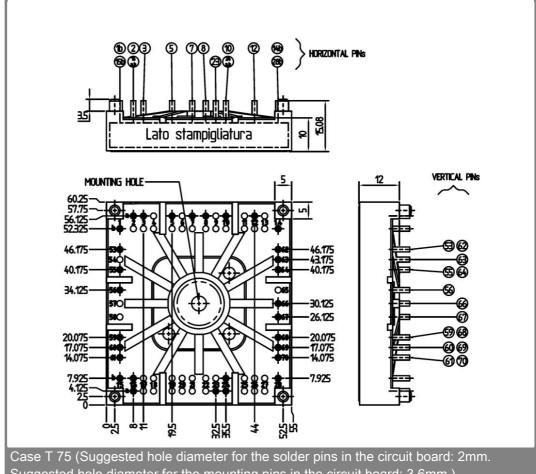












Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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